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Saxena

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(54) **POWER SEMICONDUCTOR PACKAGE**

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(51) **LOC (13) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**

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361/679.01, 713, 728, 736, 760, 761, 772,
361/775, 783, 820; 174/250, 253;
438/15, 25, 26, 51, 55, 63, 64, 106
CPC . H01L 21/00; H01L 2224/42; H01L 2224/43;
H01L 2021/00; H01L 2021/02; H01L
2021/04; H01L 21/4814; H01L 21/4846;
H01L 21/4871; H01L 21/67144; H01L
23/02; H01L 23/13; H01L 23/14; H01L
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2224/08054; H01L 23/58; H05B 41/14;
G02B 6/4201; G02B 6/4256; G02B
6/4257; G02B 6/4261; G02B 6/4262;
G02B 6/428; G02B 6/4281; H05K 1/14;
H05K 1/141; H05K 1/142; H05K 1/144;
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H05K 1/026

See application file for complete search history.

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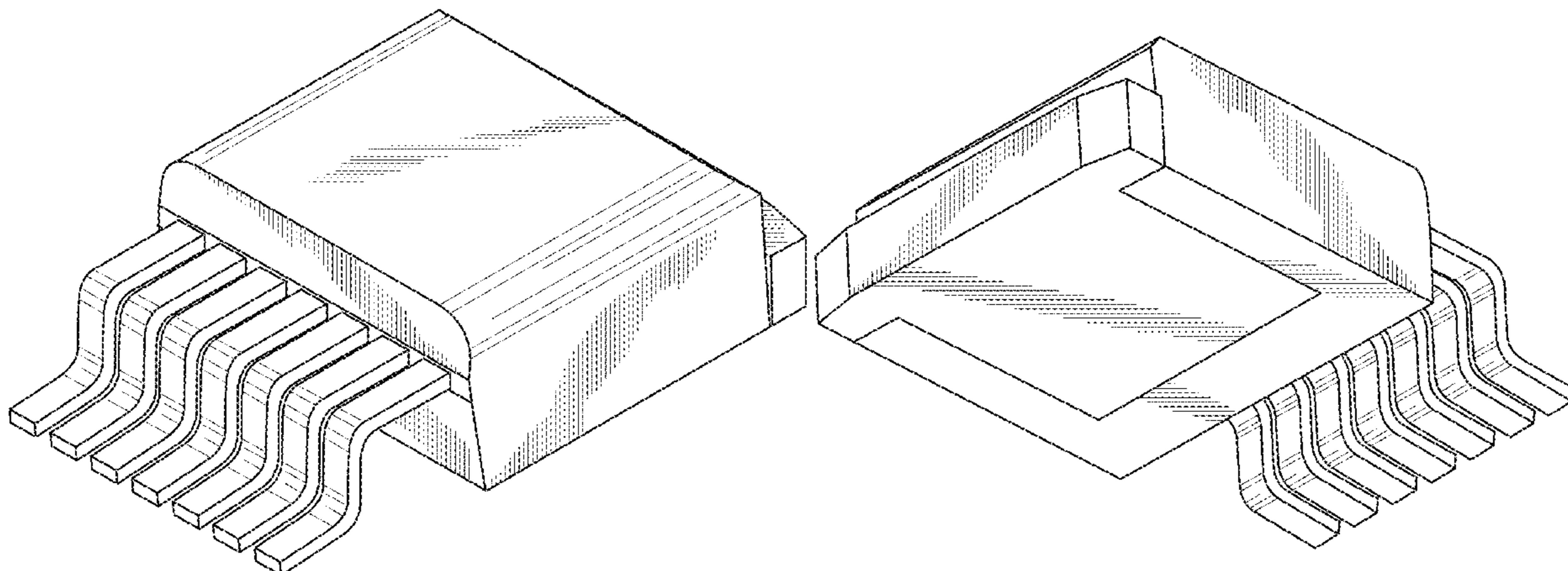
(57) **CLAIM**

The ornamental design for a power semiconductor package, as shown and described.

DESCRIPTION

FIG. 1 is a top perspective view of a power semiconductor package showing my new design;
FIG. 2 is a bottom perspective view thereof;
FIG. 3 is a top view thereof;
FIG. 4 is a bottom view thereof;
FIG. 5 is a front view thereof;
FIG. 6 is a rear view thereof;
FIG. 7 is a left side view thereof; and,
FIG. 8 is a right side view thereof.

1 Claim, 8 Drawing Sheets



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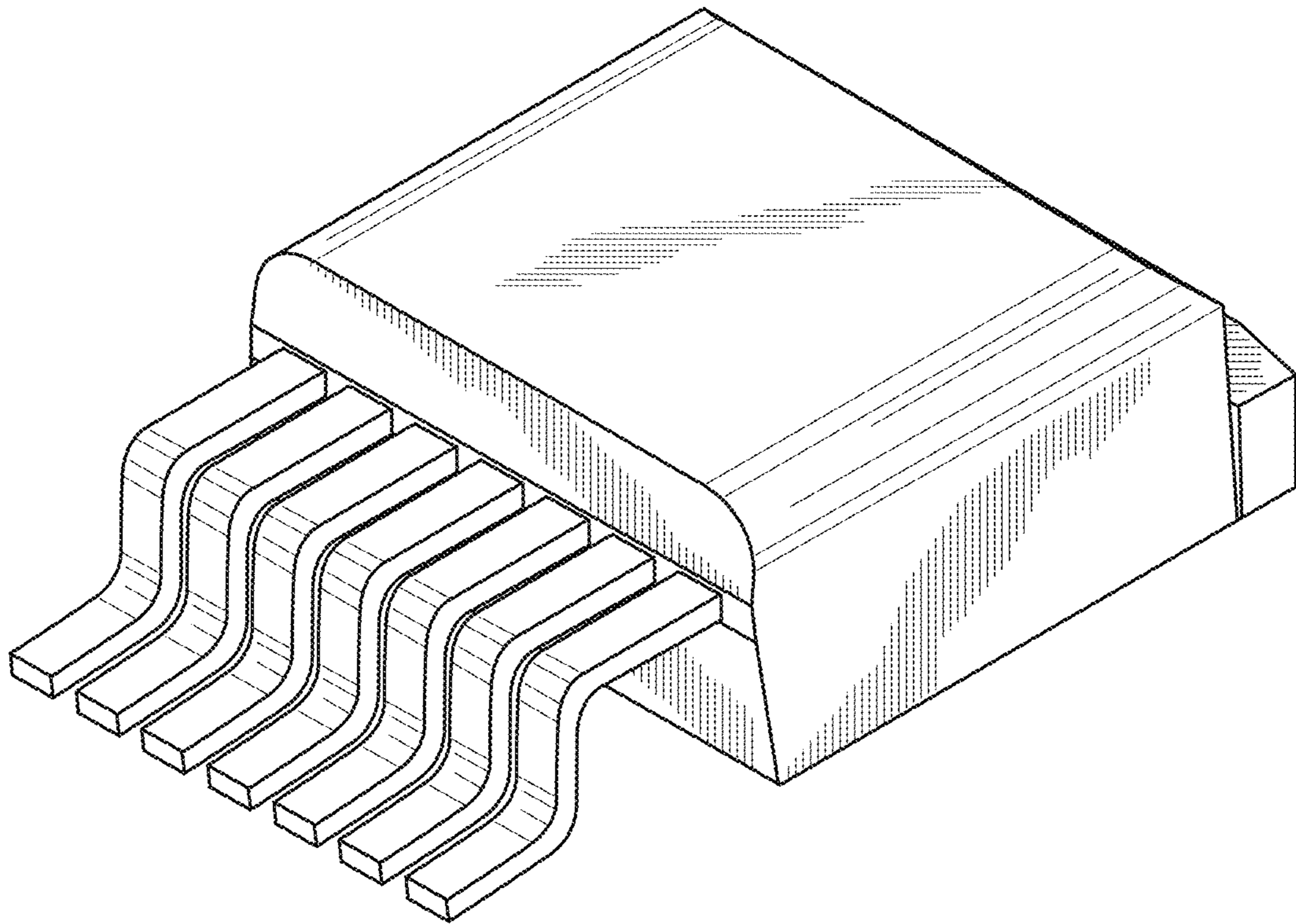


FIG. 1

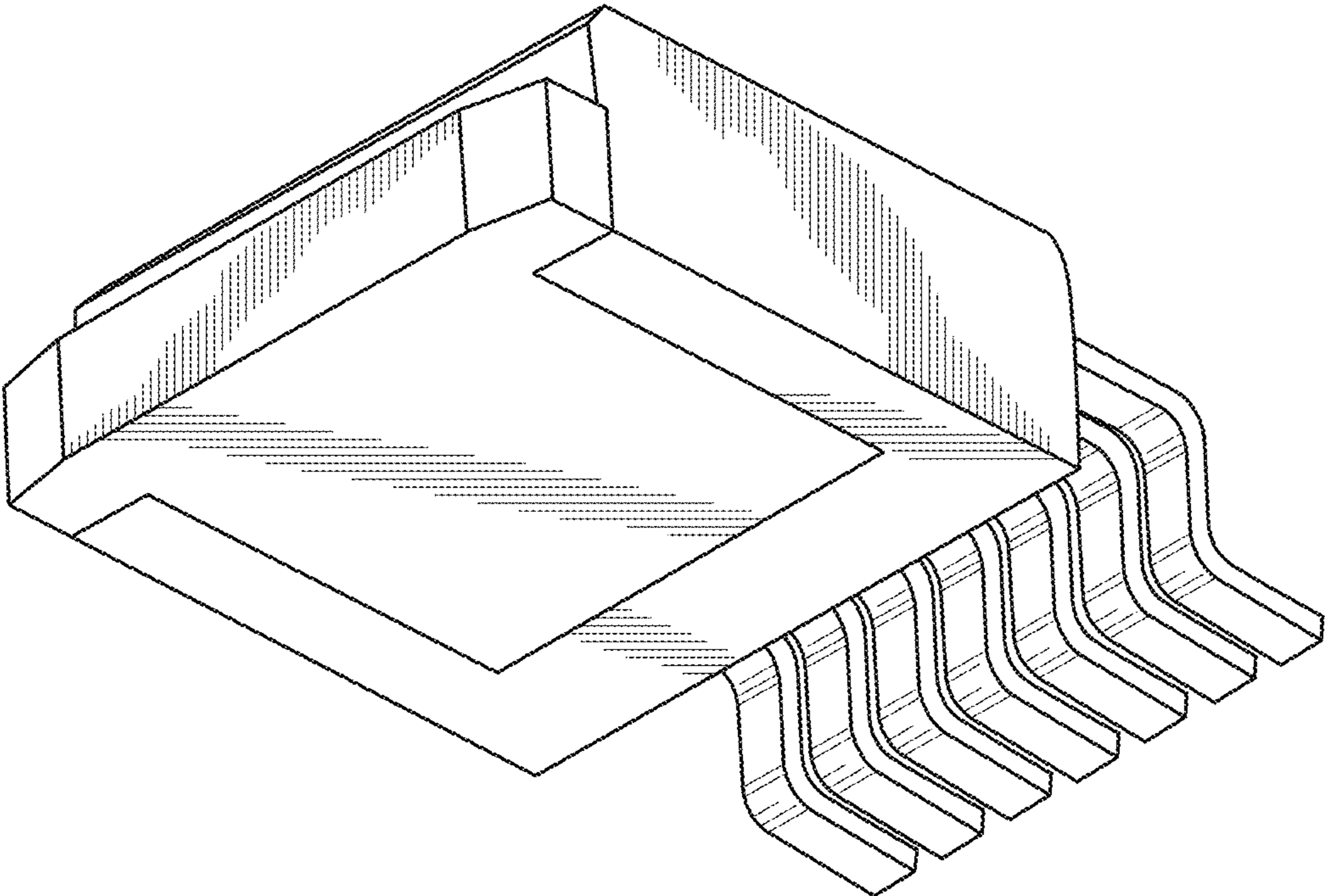


FIG. 2

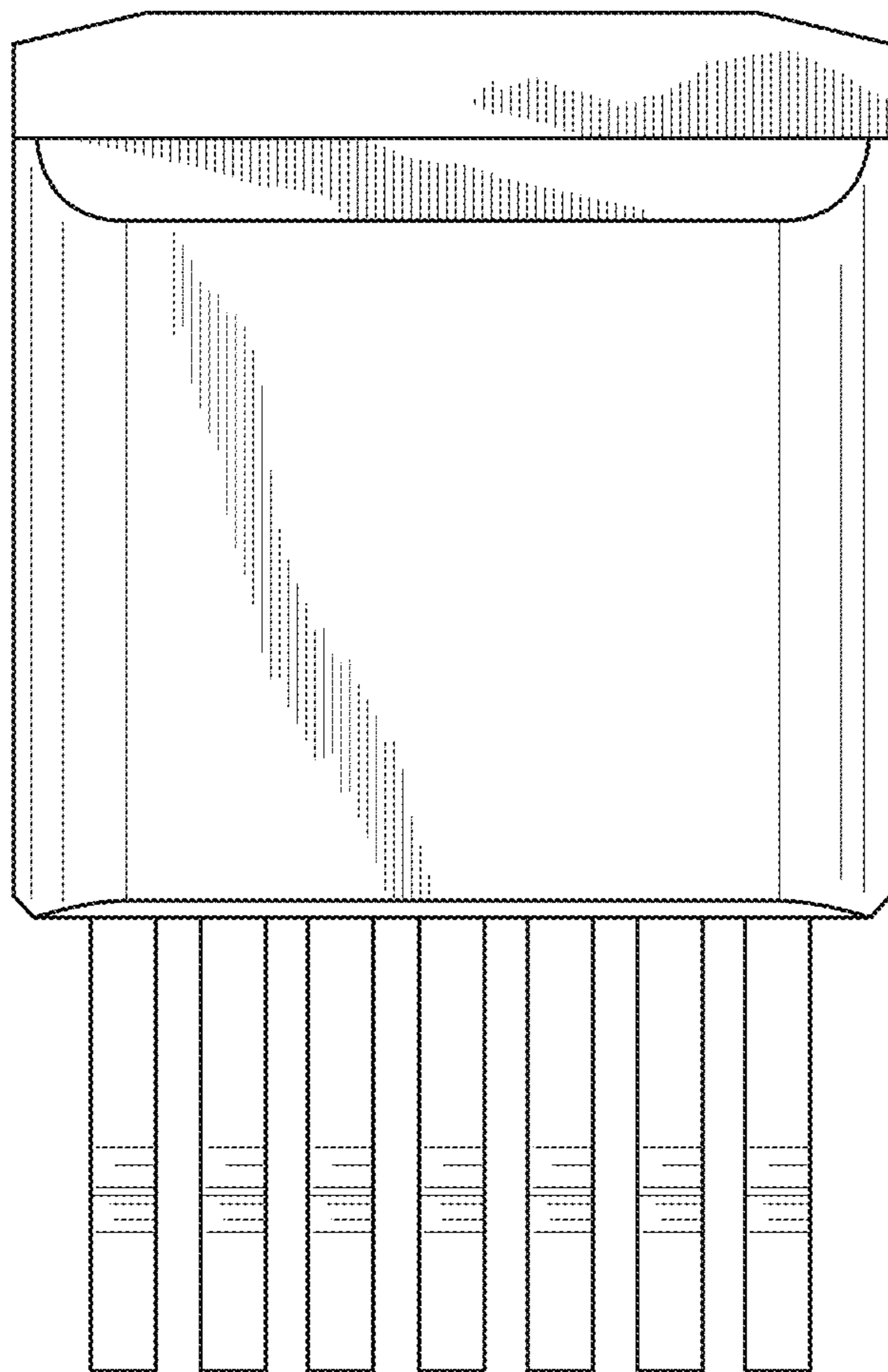


FIG. 3

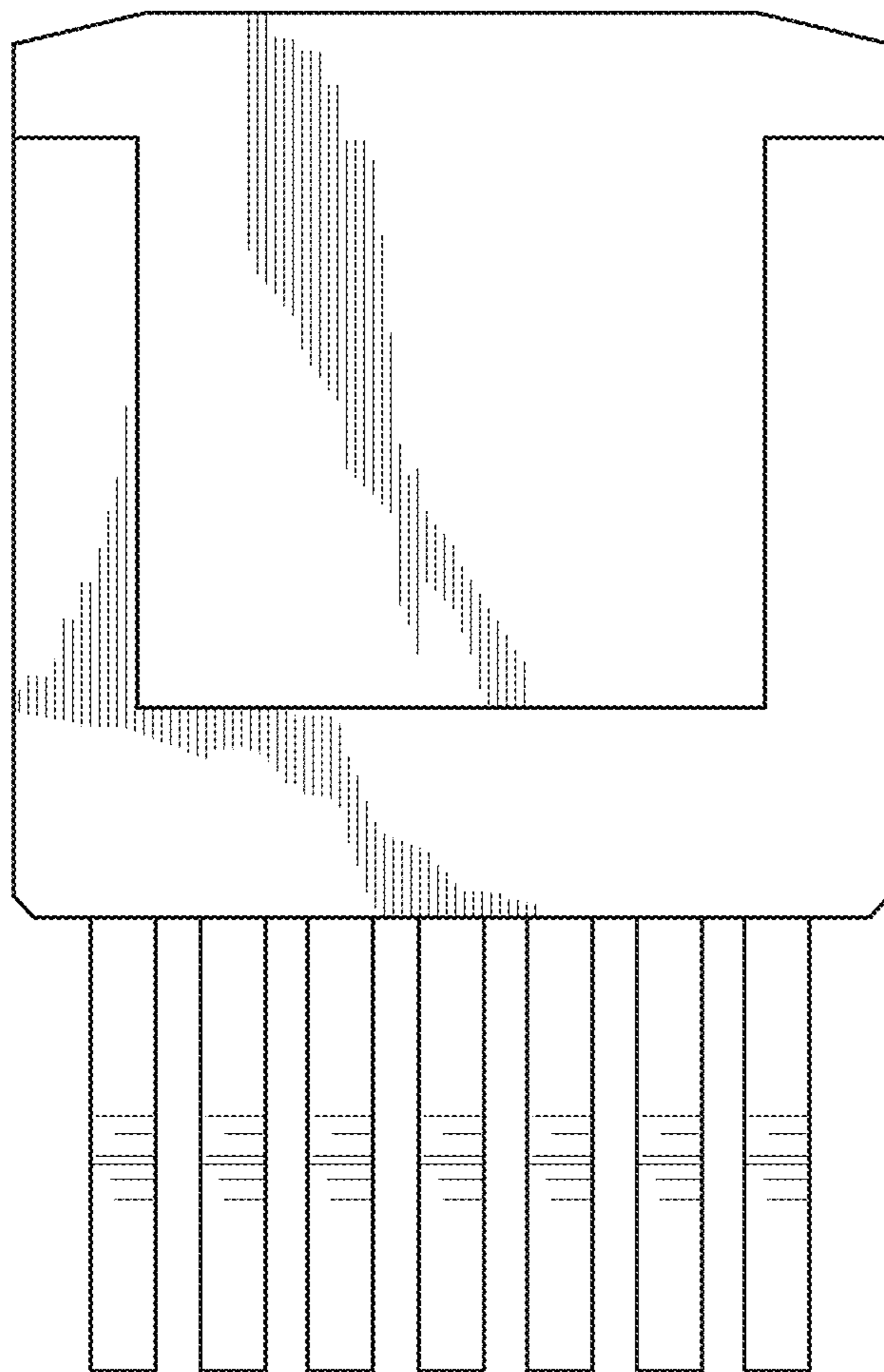


FIG. 4

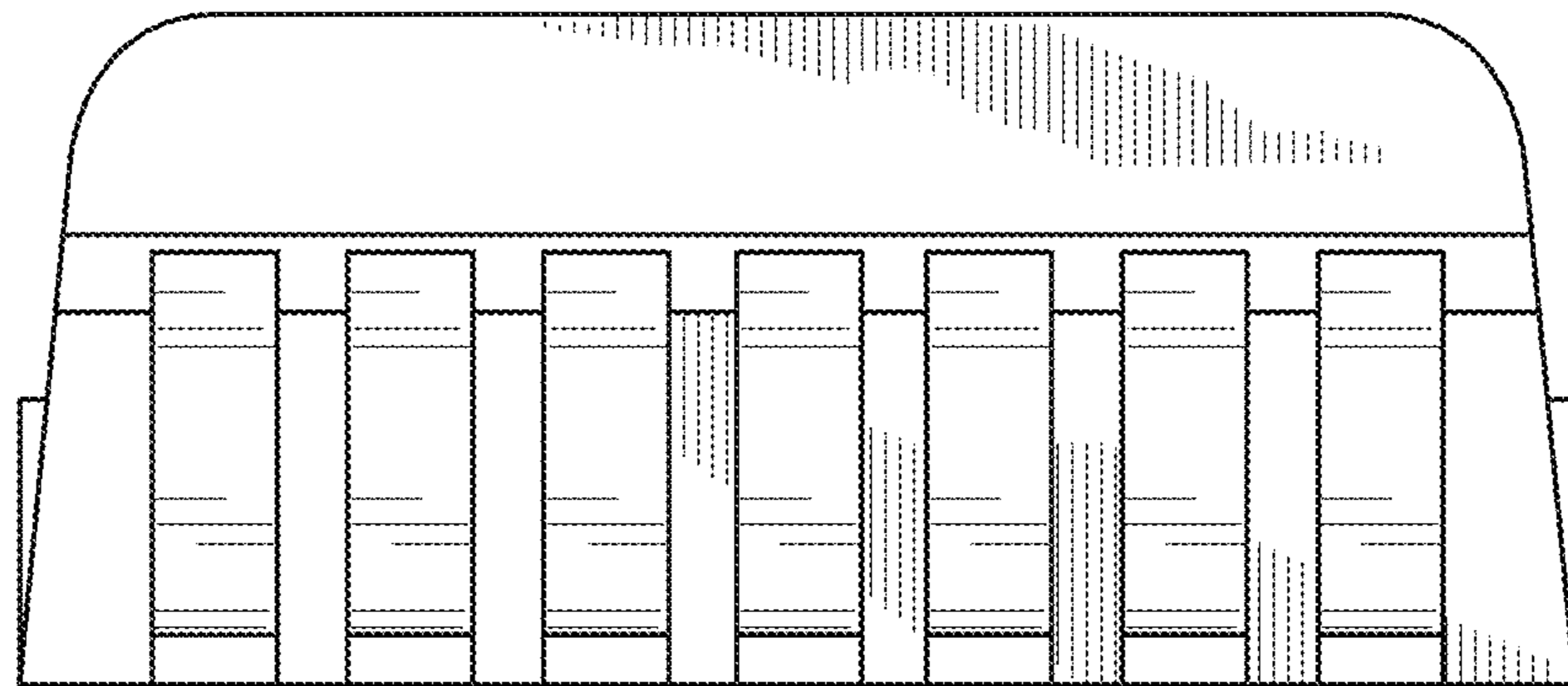


FIG. 5

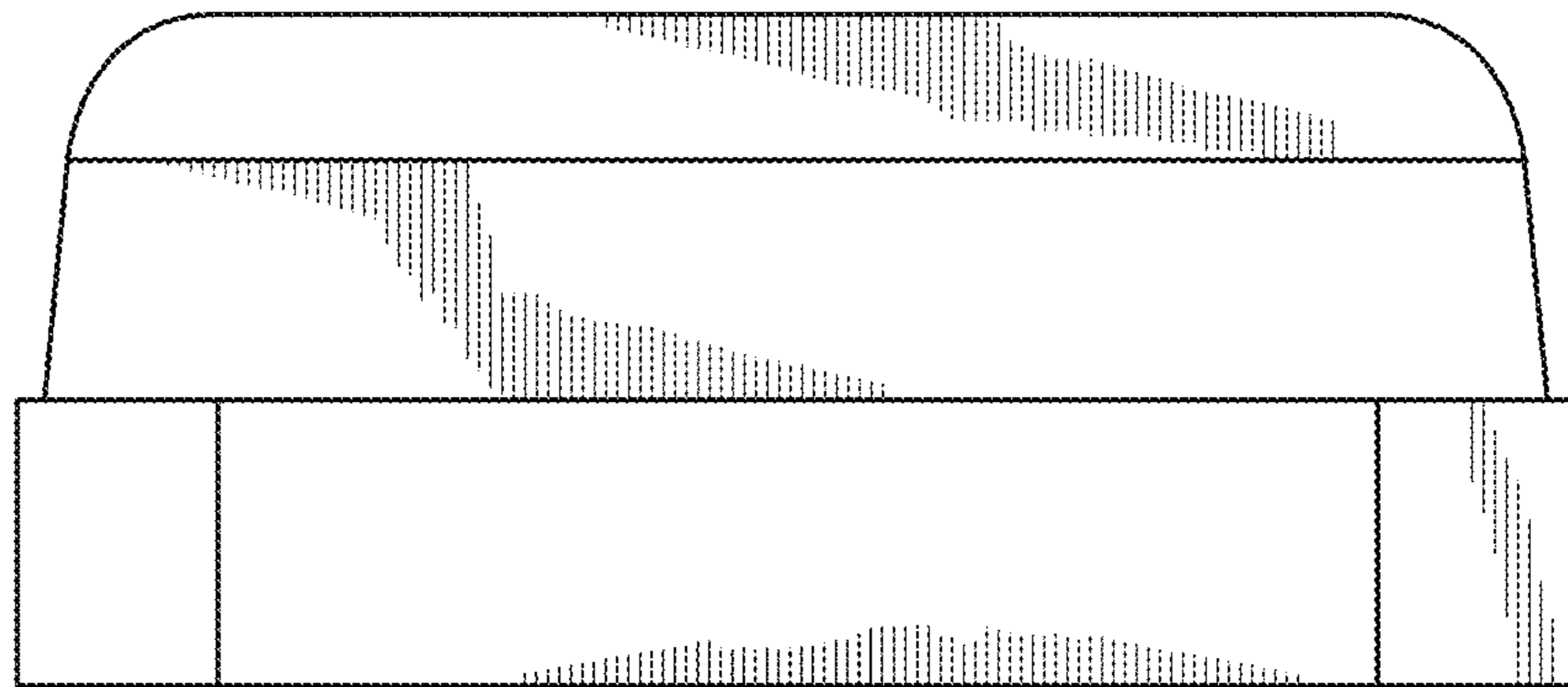


FIG. 6

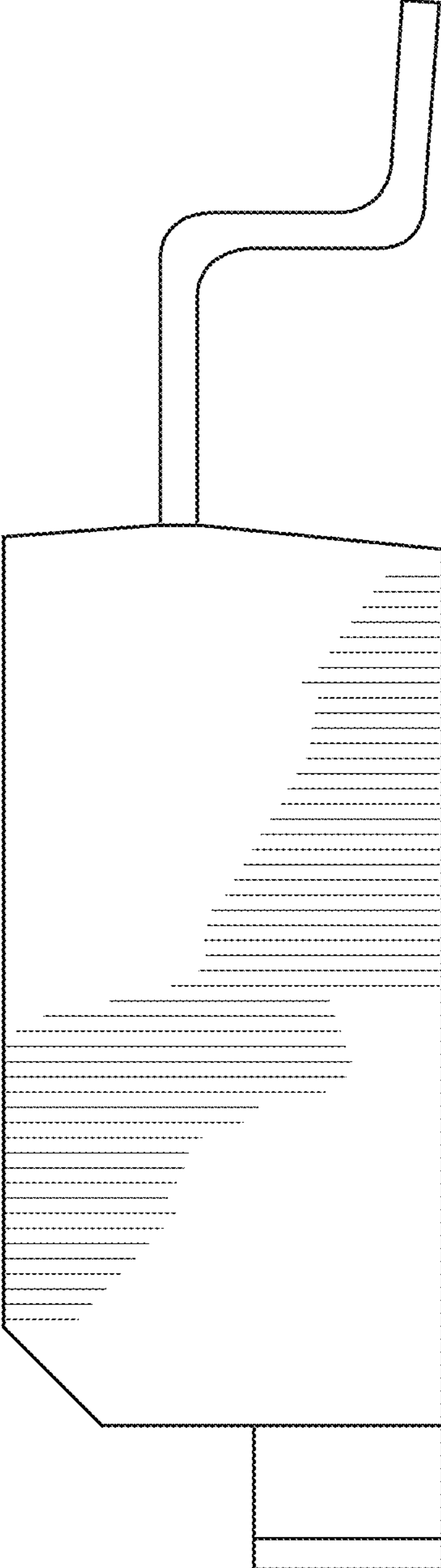


FIG. 7



FIG. 8